

Silicon PNP Power Transistors

2SA1332

DESCRIPTION

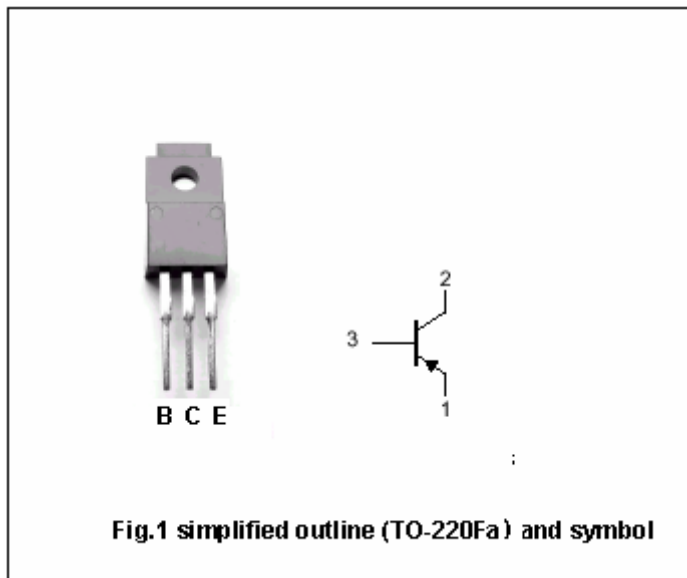
- With TO-220Fa package
- High  $V_{CEO}$

APPLICATIONS

- Power amplifier applications
- Driver stage amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector
3	Base



Absolute maximum ratings( $T_a=25^{\circ}C$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	-160	V
$V_{CEO}$	Collector-emitter voltage	Open base	-160	V
$V_{EBO}$	Emitter-base voltage	Open collector	-5	V
$I_C$	Collector current		-1.5	A
$I_B$	Base current		-0.15	A
$P_C$	Collector power dissipation	$T_C=25^{\circ}C$	20	W
$T_j$	Junction temperature		150	$^{\circ}C$
$T_{stg}$	Storage temperature		-55~150	$^{\circ}C$

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =10mA, I <sub>B</sub> =0	-160			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =1mA, I <sub>C</sub> =0	-5			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-0.5A, I <sub>B</sub> =-50mA			-1.5	V
V <sub>BE</sub>	Base-emitter voltage	I <sub>C</sub> =-0.1A; V <sub>CE</sub> =-10V			-1.0	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-160V, I <sub>E</sub> =0			-1.0	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-5V; I <sub>C</sub> =0			-1.0	μ A
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =-0.1A; V <sub>CE</sub> =-10V	60		240	
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-0.1A; V <sub>CE</sub> =-10V		200		MHz

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PACKAGE OUTLINE

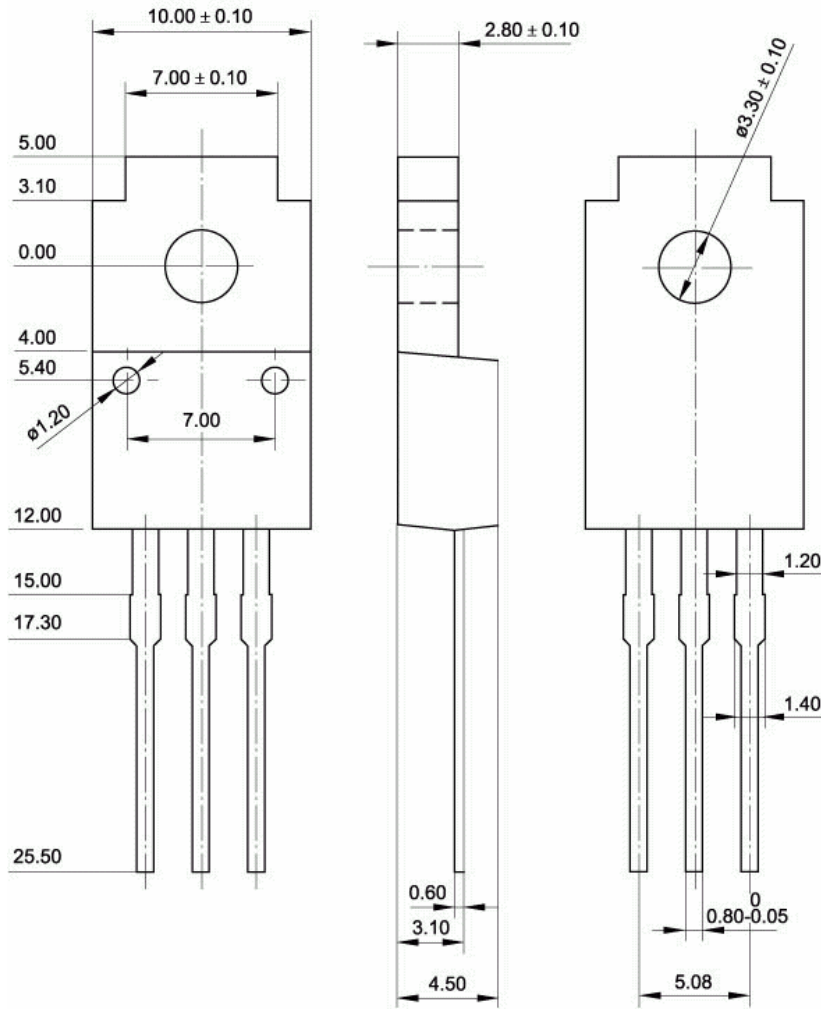


Fig.2 Outline dimensions (unindicated tolerance:  $\pm 0.15$  mm)